AMENDMENTS TO THE CLAIMS

1-8. (canceled)

9.   (original)   A mask for vapor hydrogen fluoride etching, said mask comprising a layer of patterned polyimide.

10.   (original)   The mask of claim 9 wherein said polyimide in non-photosensitive.

11.   (original)   The mask of claim 9 wherein said polyimide is photosensitive.

12.   (original)   The mask of claim 10 wherein said polyimide comprises DUPONT PI-1111.

13-26. (canceled)

27.   (currently amended)   A mask for etching, comprising a layer of material resistant to vapor hydrogen fluoride etchant patterned to expose a portion of material under said layer such that said portion can be etched by vapor hydrogen fluoride etchant, wherein said layer of material resistant to vapor hydrogen fluoride etchant comprises polyimide.

28.   (canceled)

29.   (currently amended)   The mask of Claim ~~28~~ 27 wherein said polyimide is photosensitive.

30.   (currently amended)   The mask of Claim ~~28~~ 27 wherein said polyimide is non-photosensitive.

2

31. (previously added)   The mask of Claim 27 wherein said material resistant to vapor hydrogen fluoride etchant is patterned by planerization.

32. (previously added)   The mask of Claim 27 wherein the layer of material resistant to vapor hydrogen fluoride etchant has a small opening therethrough to expose the portion of material under said layer.

33. (previously added)   The mask of Claim 32 wherein said small opening has dimensions of less than one micrometer.

34. (previously added)   An etch resistant masking layer, comprising a layer of material resistant to vapor hydrogen fluoride etchant having an opening therethrough to expose a portion of an underlying layer such that said portion can be etched by vapor hydrogen fluoride etchant.

35. (previously added)   The masking layer of Claim 34 wherein said layer of material resistant to vapor hydrogen fluoride etchant comprises polyimide.

36. (previously added)   The masking layer of Claim 35 wherein said polyimide is photosensitive.

37. (previously added)   The masking layer of Claim 35 wherein said polyimide is non-photosensitive.

38. (previously added)   The masking layer of Claim 34 wherein said opening in said material resistant to vapor hydrogen fluoride etchant is formed by planerization.

39. (previously added)   The masking layer of Claim 34 wherein said opening is less than one micrometer in width.

3

40.   (currently amended)   A mask for etching, comprising a layer of material resistant to vapor hydrogen fluoride etchant having an opening exposing a portion of material under said layer, said opening adapted to permit flow therethrough of vapor hydrogen fluoride etchant for etching said exposed portion, wherein said layer of material resistant to vapor hydrogen fluoride etchant comprises polyimide.

41.   (canceled)

42.   (currently amended)   The mask of Claim 41 40 wherein said polyimide is photosensitive.

43.   (currently amended)   The mask of Claim 41 40 wherein said polyimide is non-photosensitive.

44.   (previously added)   The mask of Claim 40 wherein said material resistant to vapor hydrogen fluoride etchant is patterned by planerization.

45.   (currently amended)   The mask of Claim 41 40 wherein said opening has dimensions of less than one micrometer.

46.   (previously added)   An intermediate structure, comprising:

a masking layer resistant to vapor hydrogen fluoride etchant having an opening therethrough;

a layer of material underlying said masking layer having a cavity formed therein by having a portion of material exposed by said opening etched by vapor hydrogen fluoride etchant; and

4

vapor hydrogen fluoride etchant in said opening and said cavity.

47.   (previously added)   The intermediate structure of Claim 46 wherein said masking layer comprises polyimide.

48.   (previously added)   The intermediate structure of Claim 47 wherein said polyimide is photosensitive.

49.   (previously added)   The intermediate structure of Claim 47 wherein said polyimide is non-photosensitive.

50.   (previously added)   The intermediate structure of Claim 46 wherein said opening has dimensions of less than one micrometer.

BOSTON 1704965v1